

## 60V N-Channel MOSFET

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
60V	5Ω@10V	340mA
	5.3Ω@4.5V	

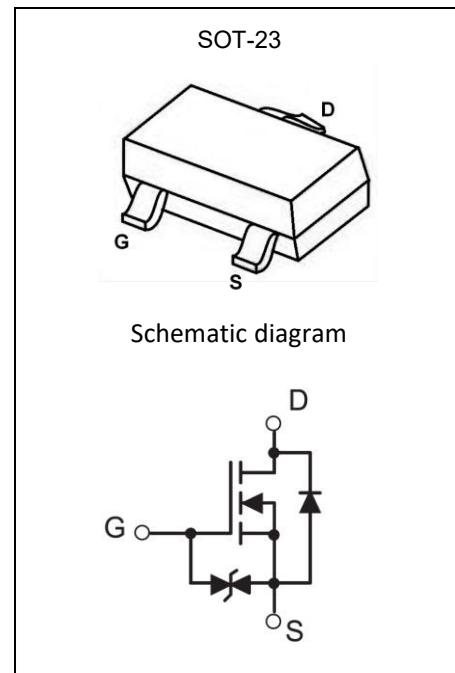
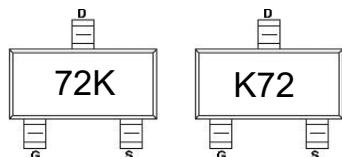
## Feature

- High density cell design for Low  $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- ESD protected GateHBM2.0KV
- AEC-Q101 qualified (Automotive grade with suffix "Q.")
- Exsemi technology

## Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

## MARKING:

ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	340	mA
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C

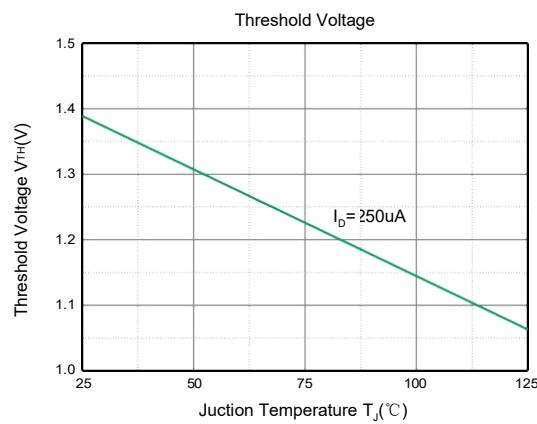
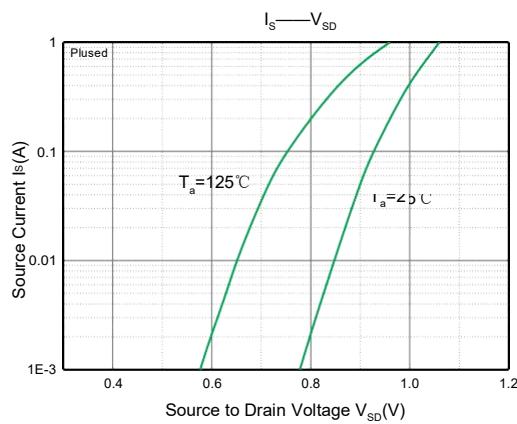
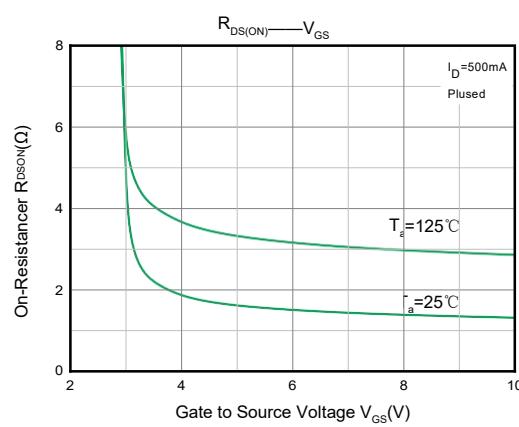
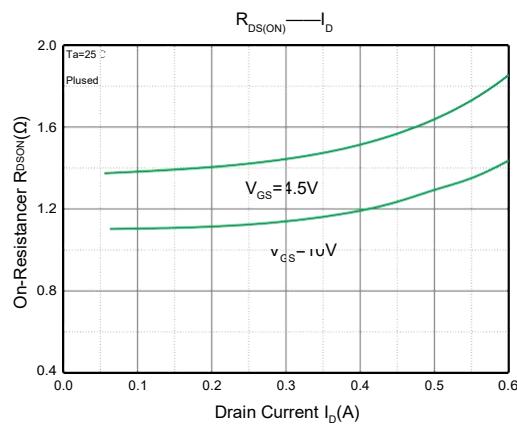
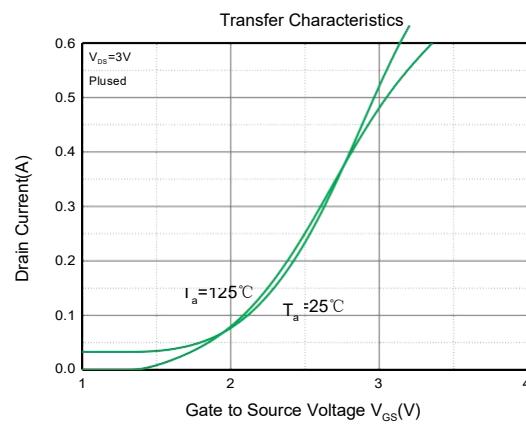
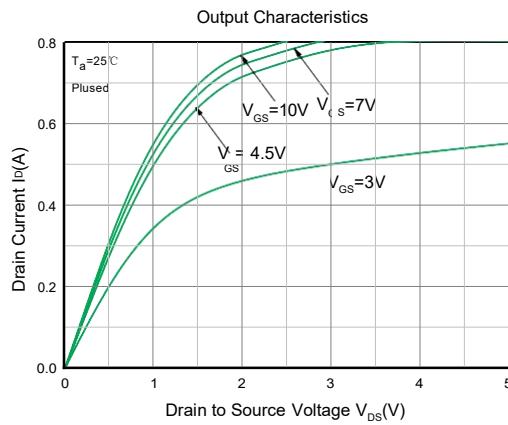
MOSFET ELECTRICAL CHARACTERISTICS( $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	60			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu\text{A}$
	$I_{GSS1}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 10$	$\mu\text{A}$
Gate-body leakage current	$I_{GSS2}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 200$	nA
	$I_{GSS2}$	$V_{GS} = \pm 5V, V_{DS} = 0V$			$\pm 100$	nA
Gate threshold voltage*	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.4	2.5	V
Drain-source on-resistance*	$R_{DS(\text{on})}$	$V_{GS} = 10V, I_D = 500\text{mA}$		1.3	5	$\Omega$
		$V_{GS} = 4.5V, I_D = 200\text{mA}$		1.4	5.3	
Recovered charge	$Q_r$	$V_{GS} = 0V, I_S = 300\text{mA}, V_R = 25V,$ $dI_s/dt = -100\text{A}/\mu\text{s}$		30		nC
<b>Dynamic characteristics**</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{MHz}$			40	pF
Output Capacitance	$C_{oss}$				30	
Reverse Transfer Capacitance	$C_{rss}$				10	
<b>Switching Characteristics**</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V, R_G = 50\Omega$ $R_{GS} = 50\Omega, R_L = 250\Omega$			10	ns
Turn-off delay time	$t_{d(off)}$				15	
Reverse recovery Time	$t_{rr}$	$V_{GS} = 0V, I_S = 300\text{mA}, V_R = 25V,$ $dI_s/dt = -100\text{A}/\mu\text{s}$		30		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 300\text{mA}$		0.97	1.5	V
<b>GATE-SOURCE ZENER DIODE</b>						
Gate-Source Breakdown Voltage	$BV_{GSO}$	$IGS = \pm 1\text{mA}(\text{Open Drain})$	$\pm 21.5$		$\pm 30$	V

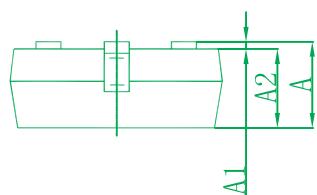
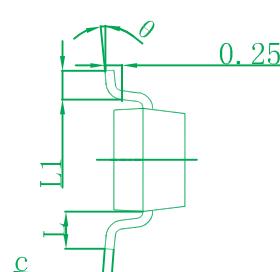
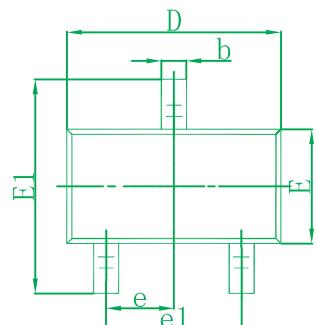
**Notes:**\*Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

\*\*These parameters have no way to verify.

## Typical Characteristics

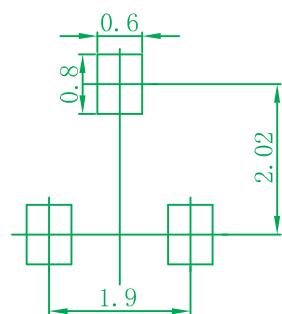


## SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.150	0.035	0.045
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.050	0.110	0.120
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.360 REF		0.014 REF	
$\theta$	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

## Ordering information

Device	Package	Shipping
2N7002K	SOT-23	3000/Tape&Reel(7inches)